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View Online at https://aerobasegroup.com/nsn/5961-01-006-9442

Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

Between 0.250 inches and 0.450 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Internal Junction Configuration:

Npn

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

300.0 breakdown voltage, collector-to-base, emitter open and 6.0 emitter to base voltage, static, collector open and 225.0 breakdown voltage, collector-to-emitter, base open

Current Rating Per Characteristic:

10.00 amperes source cutoff current and 10.00 amperes source cutoff current

Power Rating Per Characteristic:

100.0 watts small-signal input power, common-collector

Transfer Ratio:

50.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Terminal Type And Quantity:

2 pin and 1 case

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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